2SC4985

Silicon NPN epitaxial planar type

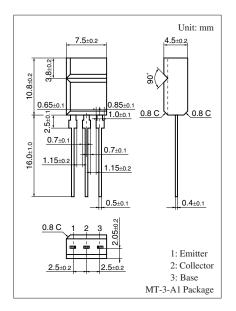
For high breakdown voltage high-speed switching

■ Features

- High collector-base voltage (Emitter open) V_{CBO}
- ullet High collector-emitter voltage (Base open) V_{CEO}
- Allowing automatic insertion with radial taping

■ Absolute Maximum Ratings $T_a = 25$ °C

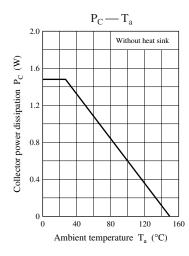
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	900	V	
Collector-emitter voltage (Base open)	V _{CEO}	800	V	
Emitter-base voltage (Collector open)	V_{EBO}	7	V	
Collector current	I_C	1	A	
Peak collector current	I_{CP}	2	A	
Collector power dissipation	P_{C}	1.5	W	
Junction temperature	T_j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

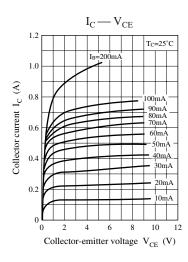


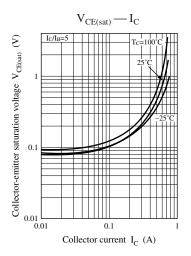
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

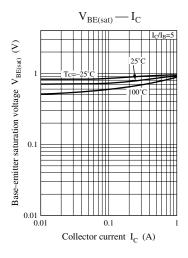
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	800			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 900 \text{ V}, I_{E} = 0$			50	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 7 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = 5 \text{ V}, I_{C} = 50 \text{ mA}$	6			_
	h _{FE2}	$V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}$	3			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 200 \text{ mA}, I_B = 40 \text{ mA}$			1.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 200 \text{ mA}, I_B = 40 \text{ mA}$			1	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_{E} = -50 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Turn-on time	t _{on}	$I_C = 200 \text{ mA}$			1	μs
Storage time	t _{stg}	$I_{B1} = 40 \text{ mA}, I_{B2} = -80 \text{ mA}$			3	μs
Fall time	t _f	$V_{CC} = 250 \text{ V}$			1	μs

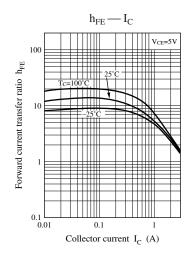
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

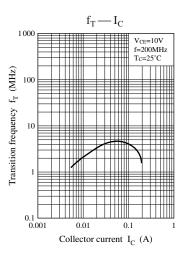












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